

b) Status of the Claims

A detailed listing of the status of the claims is presented hereafter. The status of claims 5 and 7 has been corrected from “Previously Presented” to “Withdrawn”.

1. (Previously Presented) A film-forming method for forming a deposited film on a substrate arranged in a substantially enclosed film-forming vessel by means of plasma CVD, said film-forming vessel being provided with a raw material gas introduction means and an exhaustion means, said film-forming method comprising the steps of introducing a raw material gas comprising at least a hydrogen gas and a silicon-containing raw material gas into said film-forming vessel through said raw material gas introduction means, maintaining an inner pressure of said film-forming at a desired value by means of said exhaustion means and introducing a high frequency power into said film-forming vessel through a discharge electrode provided in said film-forming vessel to generate a plasma in a plasma generation region between said substrate and said discharge electrode in said film-forming vessel thereby forming said deposited film on said substrate maintained at a desired temperature, characterized in that the formation of said deposited film on said substrate is performed while repetitively applying a periodicity voltage having at least two different waveform components having a different amplitude to an auxiliary electrode arranged at a position in said plasma generation region of said film-forming vessel.

2. (Original) The film-forming method according to claim 1, wherein the periodicity voltage has (I) a waveform component having an amplitude capable of generating mainly a radical of a silicon-containing compound and (ii) a waveform component having an amplitude capable of forming mainly a radical of hydrogen.

3. (Previously Presented) The film-forming method according to claim 1 or 2, wherein the auxiliary electrode is arranged such that said auxiliary electrode is opposed to a film-forming surface of the substrate and is situated at a position between the substrate and the discharge electrode.

4. (Original) The film-forming method according to claim 1, wherein the auxiliary electrode is arranged to be in parallel to the substrate and perpendicular to a flowing direction of the raw material gas which flows from the raw material introduction means toward the exhaustion means in the film-forming vessel.

5. (Withdrawn) A film-forming method for forming a deposited film on a substrate arranged in a substantially enclosed film-forming vessel by means of plasma CVD, said film-forming vessel being provided with a raw material gas introduction means and an exhaustion means, said film-forming method comprising the steps of introducing a raw material gas comprising at least a hydrogen gas and a silicon-containing raw material gas into said film-forming vessel through said raw material gas introduction means, maintaining an inner pressure of said film-forming at a desired value by means of said exhaustion means and introducing a high frequency power into said film-forming vessel

through a discharge electrode provided in said film-forming vessel to generate a plasma in a plasma generation region between said substrate and said discharge electrode in said film-forming vessel thereby forming said deposited film on said substrate maintained at a desired temperature, characterized in that said substrate is retained in a state of having a floating potential in said film-forming vessel, an auxiliary electrode is provided on a side opposite a film-forming face of said substrate in said film-forming vessel, such that said auxiliary electrode is electrically isolated from said substrate, and the formation of said deposited film on said substrate is performed while repetitively applying a periodicity voltage having at least two different waveform components having a different amplitude to said auxiliary electrode.

6. (Withdrawn) The film-forming method according to claim 5, wherein the periodicity voltage has (i) a waveform component having an amplitude capable of generating mainly a radical of a silicon-containing compound and (ii) a waveform component having an amplitude capable of generating mainly a radical of hydrogen.

7. (Withdrawn) The film-forming method according to claim 5 or 6, wherein the auxiliary electrode is arranged so that even when a conductive deposited film is formed on the substrate, said conductive deposited film has a potential capable of being maintained at a floating potential.

8. (Withdrawn) The film-forming method according to claim 5 or 6, wherein the auxiliary electrode is arranged such that said auxiliary electrode is parallel to

the substrate and is perpendicular to a flowing direction the raw material gas which flows from the raw material gas introduction means toward the exhaustion means in the film-forming vessel.

9. (Cancelled)